

Angela Thrnhardt

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48
papers

689
citations

13
h-index

25
g-index

71
ext. papers

754
ext. citations

2.8
avg, IF

2.78
L-index

#	Paper	IF	Citations
48	Clustering effects in Ga(AsBi). <i>Applied Physics Letters</i> , 2010 , 96, 131115	3.4	116
47	Measurement of optical absorption by a single quantum dot exciton. <i>Physical Review B</i> , 2002 , 65,	3.3	106
46	Relation between dipole moment and radiative lifetime in interface fluctuation quantum dots. <i>Physical Review B</i> , 2002 , 65,	3.3	76
45	Quantum theory of phonon-assisted exciton formation and luminescence in semiconductor quantum wells. <i>Physical Review B</i> , 2000 , 62, 2706-2720	3.3	59
44	Nitrogen incorporation effects on gain properties of GaInNAs lasers: Experiment and theory. <i>Applied Physics Letters</i> , 2005 , 86, 201117	3.4	30
43	Microscopic theory of the optical properties of Ga(AsBi)/GaAs quantum wells. <i>Semiconductor Science and Technology</i> , 2008 , 23, 125009	1.8	27
42	Luminescence dynamics in Ga(AsBi). <i>Applied Physics Letters</i> , 2011 , 98, 161104	3.4	26
41	Nonequilibrium gain in optically pumped GaInNAs laser structures. <i>Applied Physics Letters</i> , 2004 , 85, 5526-5528	3.4	24
40	Time-resolved photoluminescence of type-I and type-II (GaIn)As/Ga(NAs) heterostructures. <i>Physical Review B</i> , 2005 , 71,	3.3	17
39	Evidence of two disorder scales in Ga(AsBi). <i>Physica Status Solidi (B): Basic Research</i> , 2011 , 248, 851-854	1.3	15
38	Type I-type II transition in InGaAs/GaNAs heterostructures. <i>Applied Physics Letters</i> , 2005 , 86, 081903	3.4	15
37	An optimized digital alloy growth technique for accurate band gap engineering. <i>Journal of Crystal Growth</i> , 1999 , 201-202, 163-165	1.6	14
36	Numerical study of the influence of an antireflection coating on the operating properties of vertical-external-cavity surface-emitting lasers. <i>Journal of Applied Physics</i> , 2009 , 106, 063105	2.5	13
35	Microscopic calculation and measurement of the laser gain in a (GaIn)Sb quantum well structure. <i>Applied Physics Letters</i> , 2008 , 92, 071107	3.4	11
34	Dynamic behavior of 1040nm semiconductor disk lasers on a nanosecond time scale. <i>Applied Physics Letters</i> , 2007 , 90, 241102	3.4	11
33	Gain and carrier losses of (GaIn)(NAs) heterostructures in the 1300-1550 nm range. <i>Applied Physics Letters</i> , 2005 , 87, 261109	3.4	10
32	Coherent dynamics of photoexcited semiconductor superlattices in homogeneous electric fields. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 7, 267-273	3	10

31	Field-dependent absorption in superlattices: Comparison of theory and experiment. <i>Applied Physics Letters</i> , 1998 , 73, 2612-2614	3.4	9
30	Microscopic electroabsorption line shape analysis for Ga(AsSb) _{1-x} GaAs heterostructures. <i>Journal of Applied Physics</i> , 2007 , 101, 033118	2.5	8
29	Interplay of phonon and disorder scattering in semiconductor quantum wells. <i>Physical Review B</i> , 2003 , 68,	3.3	8
28	Quantum modeling of semiconductor gain materials and vertical-external-cavity surface-emitting laser systems. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 789-808	1.3	7
27	Interband Transitions in InGaN Quantum Wells 145-167		7
26	Transient gain spectroscopy of (GaIn)As quantum wells: Experiment and microscopic analysis. <i>Applied Physics Letters</i> , 2007 , 90, 251102	3.4	7
25	Bismuth-containing III ^V semiconductors 2013 , 139-158		6
24	Microscopic Modeling of Quantum Well Gain Media for VECSEL Applications. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2009 , 15, 984-992	3.8	6
23	Interplay between coherent and incoherent scattering in quantum well secondary emission. <i>Physical Review B</i> , 2000 , 62, 16802-16807	3.3	6
22	Calculation of the excitonic absorption in parabolic semiconductor quantum-well structures. <i>Physical Review B</i> , 1998 , 58, 1512-1516	3.3	6
21	Anisotropic emission of interface fluctuation quantum dots. <i>European Physical Journal B</i> , 2002 , 27, 571-576		4
20	A study of light-hole electro-absorption in AlGaAs parabolic quantum wells, using a novel method. <i>Superlattices and Microstructures</i> , 1999 , 25, 425-429	2.8	4
19	Hole system heating by ultrafast interband energy transfer in optically excited Ge/SiGe quantum wells. <i>Physical Review B</i> , 2012 , 85,	3.3	3
18	Microscopic simulation of nonequilibrium features in quantum-well pumped semiconductor disk lasers. <i>Applied Physics Letters</i> , 2010 , 96, 051116	3.4	3
17	Hole confinement in quantum islands in Ga(AsSb) _{1-x} GaAs/(AlGa)As heterostructures. <i>Applied Physics Letters</i> , 2008 , 92, 161101	3.4	3
16	Microscopic modeling of the optical properties of semiconductor nanostructures. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 2480-2483	3.9	3
15	Carrier Dynamics in Quantum Well Lasers. <i>Optical and Quantum Electronics</i> , 2006 , 38, 361-368	2.4	3
14	Modeling mode competition in laser diodes. <i>Optical and Quantum Electronics</i> , 2019 , 51, 1	2.4	2

13	Phonon-assisted transitions and optical gain in indirect semiconductors. <i>Physical Review B</i> , 2010 , 82,	3.3	2
12	Influence of chirp on the femtosecond excitation of a semiconductor microcavity laser. <i>Applied Physics Letters</i> , 2008 , 92, 011107	3.4	2
11	Microscopic simulation of semiconductor lasers at telecommunication wavelengths. <i>Optical and Quantum Electronics</i> , 2007 , 38, 1005-1009	2.4	2
10	Coherent and Incoherent Contributions to Secondary Emission. <i>Physica Status Solidi (B): Basic Research</i> , 2000 , 221, 227-230	1.3	2
9	Gain and Absorption: Many-Body Effects 2005 , 1-25		1
8	Many-Body Quantum Theory of Spontaneous Emission of Semiconductor Quantum Wells. <i>Physica Status Solidi A</i> , 2000 , 178, 409-416		1
7	Modelling of the Laser Dynamics of an (Al,In)GaN Laser Diode 2018 ,		1
6	Do equidistant energy levels necessitate a harmonic potential?. <i>Optical and Quantum Electronics</i> , 2021 , 53, 1	2.4	1
5	Mode rolling effects in nitride laser diodes. <i>Engineering Research Express</i> , 2020 , 2, 035036	0.9	0
4	Holes in germanium quantum wells: spin relaxation and temperature dynamics. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1238-1241		
3	Ga(AsSb)/GaAs/(AlGa)As heterostructures: additional hole-confinement due to quantum islands. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 411-414		
2	Performance changes of a vertical-external-cavity surfaceemitting laser by an intra-cavity anti-reflex-coating. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 572-575		
1	Kinetic Monte-Carlo Simulation of Exciton Hopping: Urbach Tails in Gas-Molecule Decorated MoSe ₂ . <i>Physica Status Solidi (B): Basic Research</i> , 2021 , 258, 2100186	1.3	